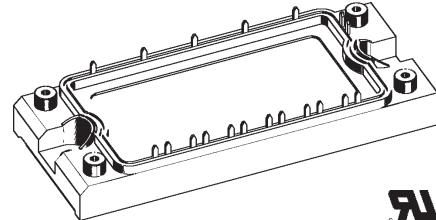
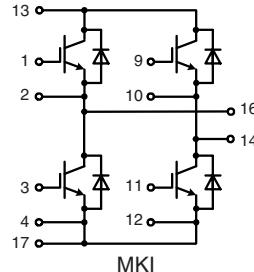


IGBT Modules

H Bridge

Short Circuit SOA Capability
Square RBSOA

I_{C25} = 65 A
 V_{CES} = 1200 V
 $V_{CE(sat)\text{typ.}}$ = 3.2 V



IGBTs

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}		± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	65		A
I_{C80}	$T_C = 80^\circ\text{C}$	45		A
I_{CM}	$V_{GE} = \pm 15 \text{ V}$; $R_G = 13 \Omega$; $T_{VJ} = 125^\circ\text{C}$	100		A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$		V_{CES}	
t_{sc}	$V_{CE} = 900 \text{ V}$; $V_{GE} = \pm 15 \text{ V}$; $R_G = 13 \Omega$; $T_{VJ} = 125^\circ\text{C}$ SCSOA; non-repetitive	10		μs
P_{tot}	$T_C = 25^\circ\text{C}$	350		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 50 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	3.2	3.8	V
		3.8		V
$V_{GE(\text{th})}$	$I_C = 2 \text{ mA}$; $V_{GE} = V_{CE}$	4.5		V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.7 mA	mA
		2.5		mA
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$		500 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	$\left. \begin{array}{l} \text{Inductive load, } T_{VJ} = 125^\circ\text{C} \\ V_{CE} = 600 \text{ V}; I_C = 50 \text{ A} \\ V_{GE} = \pm 15 \text{ V}; R_G = 13 \Omega \end{array} \right\}$	130		ns
		60		ns
		360		ns
		30		ns
		6.0		mJ
		2.5		mJ
C_{ies} Q_{Gon}	$V_{CE} = 25 \text{ V}$; $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$ $V_{CE} = 600 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 50 \text{ A}$	3.3		nF
		600		nC
R_{thJC}	(per IGBT)		0.35	K/W

Features

- Fast NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED™ diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate
 - UL registered, E 72873

Typical Applications

- motor control
 - . DC motor amature winding
 - . DC motor excitation winding
 - . synchronous motor excitation winding
- supply of transformer primary winding
- . power supplies
- . welding
- . X-ray
- . battery charger

Diodes

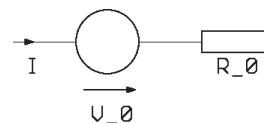
Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	110	A	
I _{F80}	T _C = 80°C	70	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 50 A; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C	2.2	2.6	V
		1.6		V
I _{RM} t _{rr}	I _F = 50 A; di _F /dt = -500 A/μs; T _{VJ} = 125°C V _R = 600 V; V _{GE} = 0 V	40		A
		200		ns
R _{thJC}	(per diode)		0.61	K/W

Module

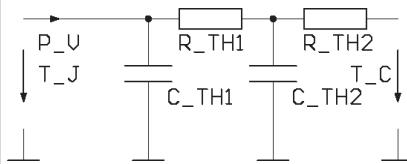
Symbol	Conditions	Maximum Ratings		
T _{VJ}	operating	-40...+125		°C
T _{VJM}		-40...+150		°C
T _{stg}		-40...+125		°C
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500		V~
M _d	Mounting torque (M5)	2.7 - 3.3		Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R _{pin-chip}		5		mΩ
d _s	Creepage distance on surface	6		mm
d _A	Strike distance in air	6		mm
R _{thCH}	with heatsink compound	0.02		K/W
Weight		180		g

Equivalent Circuits for Simulation**Conduction**

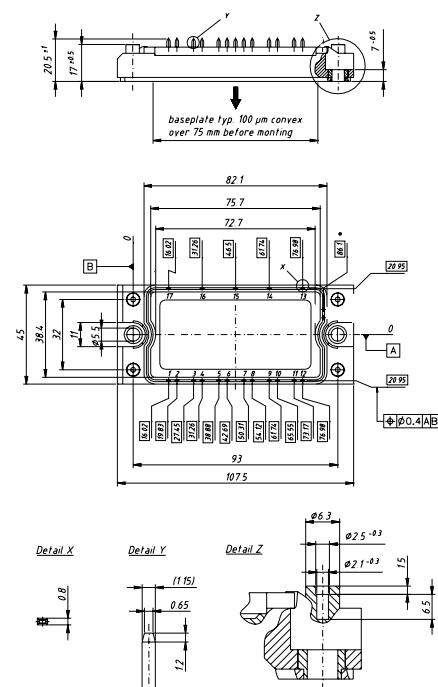
IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V₀ = 2.05 V; R₀ = 35 mΩ

Free Wheeling Diode (typ. at T_J = 125°C)
V₀ = 1.3 V; R₀ = 6 mΩ

Thermal Response

IGBT (typ.)
C_{th1} = 0.22 J/K; R_{th1} = 0.26 K/W
C_{th2} = 1.74 J/K; R_{th2} = 0.09 K/W

Free Wheeling Diode (typ.)
C_{th1} = 0.151 J/K; R_{th1} = 0.483 K/W
C_{th2} = 1.003 J/K; R_{th2} = 0.127 K/W

Dimensions in mm (1 mm = 0.0394")

pins 5, 6, 7, 8 and 15 for MWI only